2N6487, 2N6488 (NPN), 2N6490, 2N6491 (PNP)

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted) (Note 2)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage (Note 3) ($I_C = 200 \text{ mAdc}, I_B = 0$) 2N6487, 2N6490 2N6488, 2N6491	V _{CEO(sus)}	60 80		Vdc
Collector–Emitter Sustaining Voltage (Note 3) (I _C = 200 mAdc, V _{BE} = 1.5 Vdc) 2N6487, 2N6490 2N6488, 2N6491	V _{CEX}	70 90		Vdc
Collector Cutoff Current (V _{CE} = 30 Vdc, I _B = 0) 2N6487, 2N6490 (V _{CE} = 40 Vdc, I _B = 0) 2N6488, 2N6491	ICEO	-	1.0 1.0	mAdc
Collector Cutoff Current ($V_{CE} = 65 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc}$) 2N6487, 2N6490 ($V_{CE} = 85 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc}$) 2N6488, 2N6491 ($V_{CE} = 60 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc}, T_C = 150^{\circ}\text{C}$) 2N6487, 2N6490 ($V_{CE} = 80 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc}, T_C = 150^{\circ}\text{C}$) 2N6488, 2N6491	ICEX	- - -	500 500 5.0 5.0	μAdc
Emitter Cutoff Current ($V_{BE} = 5.0 \text{ Vdc}, I_C = 0$)	I _{EBO}	_	1.0	mAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 5.0 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc}$) ($I_C = 15 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc}$)	h _{FE}	20 5.0	150 -	-
Collector–Emitter Saturation Voltage ($I_C = 5.0 \text{ Adc}, I_B = 0.5 \text{ Adc}$) ($I_C = 15 \text{ Adc}, I_B = 5.0 \text{ Adc}$)	V _{CE(sat)}		1.3 3.5	Vdc
Base-Emitter On Voltage ($I_C = 5.0 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc}$) ($I_C = 15 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc}$)	V _{BE(on)}		1.3 3.5	Vdc
DYNAMIC CHARACTERISTICS	·	•	•	•
Current–Gain – Bandwidth Product (Note 4) ($I_C = 1.0 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc}, f_{test} = 1.0 \text{ MHz}$)	fT	5.0	_	MHz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

h_{fe}

25

_

_

2. Indicates JEDEC Registered Data.

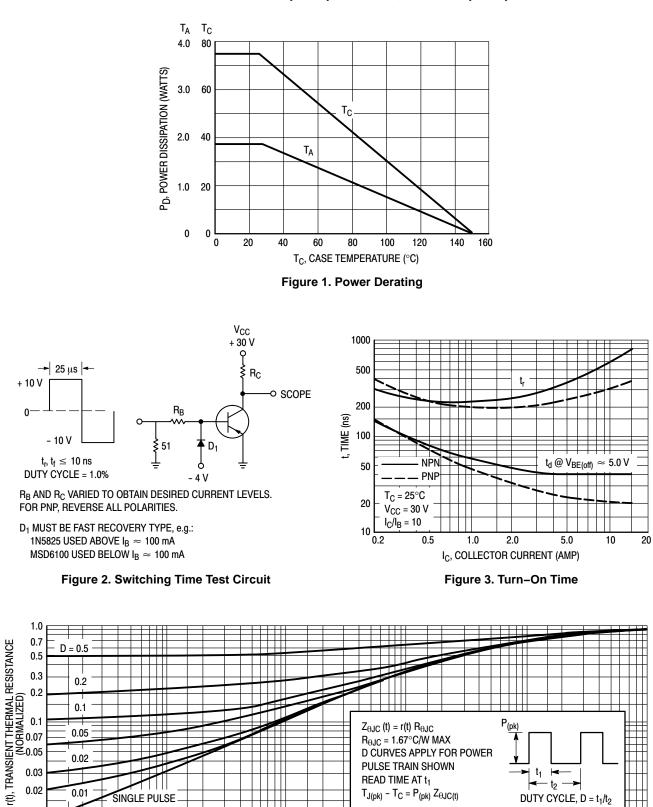
Small-Signal Current Gain

3. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%.

 $(I_{C} = 1.0 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc}, f = 1.0 \text{ kHz})$

4. $f_T = |h_{fe}| \bullet f_{test}$

2N6487, 2N6488 (NPN), 2N6490, 2N6491 (PNP)



2.0

1.0

PULSE TRAIN SHOWN

 $T_{J(pk)} - T_C = P_{(pk)} Z_{\Theta JC(t)}$

10

20

READ TIME AT t₁

5.0

t, TIME (ms) **Figure 4. Thermal Response** t₁ |←

100

50

t₂

DUTY CYCLE, $D = t_1/t_2$

200

500 1.0 k

0.02

0.01

0.02

0.01 🛏 0.01

SINGLE PULSE

0.05

0.1

0.2

0.5

2N6487, 2N6488 (NPN), 2N6490, 2N6491 (PNP)

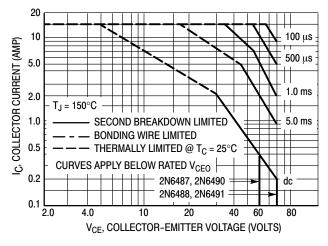


Figure 5. Active–Region Safe Operating Area

There are two limitations on the power handling ability of a transistors average junction temperature and second breakdown. Safe operating area curves indicate I_C-V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^{\circ}C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

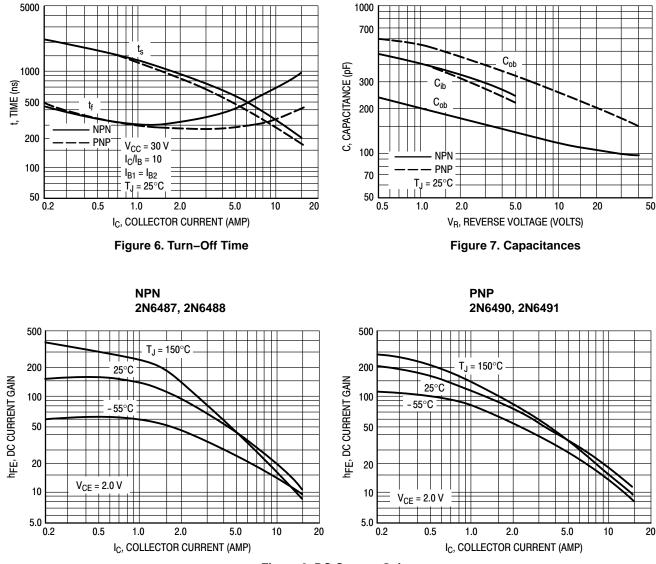


Figure 8. DC Current Gain

2N6487, 2N6488 (NPN), 2N6490, 2N6491 (PNP)

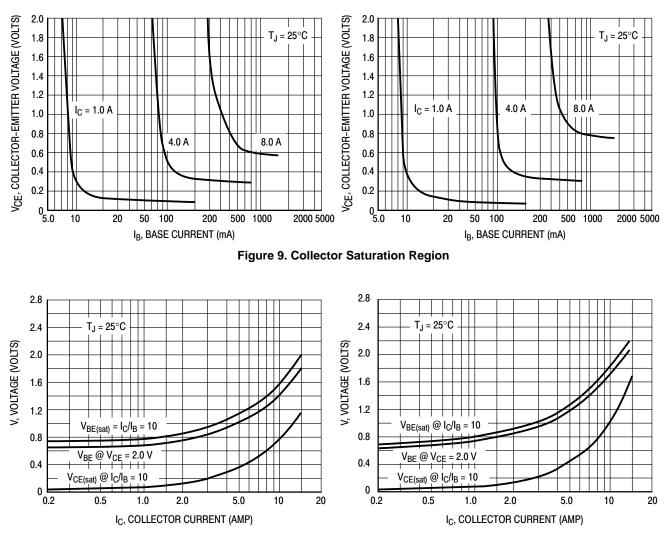


Figure 10. "On" Voltages

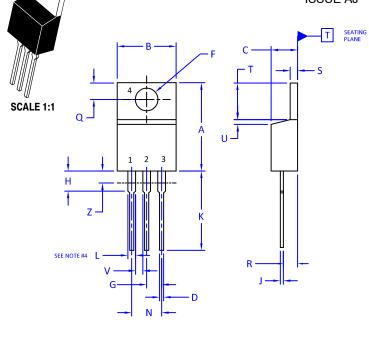
ORDERING INFORMATION

Device	Device Marking	Package	Shipping
2N6487G	2N6487	TO-220 (Pb-Free)	50 Units / Rail
2N6488G	2N6488	TO-220 (Pb-Free)	50 Units / Rail
2N6490G	2N6490	TO-220 (Pb-Free)	50 Units / Rail
2N6491G	2N6491	TO-220 (Pb-Free)	50 Units / Rail

DATE 05 NOV 2019



TO-220 CASE 221A-09 ISSUE AJ



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.

2. CONTROLLING DIMENSION: INCHES

3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

4. MAX WIDTH FOR F102 DEVICE = 1.35MM

	INCH	INCHES MILLIM		ETERS	
DIM	MIN.	MAX.	MIN.	MAX.	
А	0.570	0.620	14.48	15.75	
В	0.380	0.415	9.66	10.53	
С	0.160	0.190	4.07	4.83	
D	0.025	0.038	0.64	0.96	
F	0.142	0.161	3.60	4.09	
G	0.095	0.105	2.42	2.66	
Н	0.110	0.161	2.80	4.10	
J	0.014	0.024	0.36	0.61	
К	0.500	0.562	12.70	14.27	
L	0.045	0.060	1.15	1.52	
Ν	0.190	0.210	4.83	5.33	
Q	0.100	0.120	2.54	3.04	
R	0.080	0.110	2.04	2.79	
S	0.045	0.055	1.15	1.41	
Т	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
V	0.045		1.15		
Z		0.080		2.04	

STYLE 1: PIN 1. 2. 3. 4.	COLLECTOR EMITTER	STYLE 2: PIN 1. 2. 3. 4.	EMITTER	3.	CATHODE ANODE GATE ANODE	STYLE 4: PIN 1. 2. 3. 4.	MAIN TERMINAL 1 MAIN TERMINAL 2 GATE MAIN TERMINAL 2
STYLE 5: PIN 1. 2. 3. 4.	DRAIN SOURCE	2. 3.	ANODE CATHODE ANODE CATHODE	2. 3.	CATHODE ANODE CATHODE ANODE	STYLE 8: PIN 1. 2. 3. 4.	
STYLE 9: PIN 1. 2. 3. 4.	COLLECTOR EMITTER	STYLE 10: PIN 1. 2. 3. 4.	GATE SOURCE DRAIN	STYLE 11: PIN 1. 2. 3. 4.	DRAIN SOURCE GATE	STYLE 12 PIN 1. 2. 3. 4.	MAIN TERMINAL 1 MAIN TERMINAL 2 GATE NOT CONNECTED

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